NSN 5962-01-253-0169

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-253-0169

Body Length:	
1.290 inches	
Body Width:	
0.610 inches	
Body Height:	
0.150 inches	
Maximum Power Dissip	pation Rating:
1.0 watts	
Operating Tempurature	Range:
-55.0/+125.0 degrees ce	Isius
Storage Tempurature R	ange:
-65.0/+150.0 degrees ce	Isius
End Application:	
Radar set an/sps-4 (v) 5	
Features Provided:	
Schottky and programma	able and bipolar
Inclosure Material:	
Ceramic	
Inclosure Configuration	1:
Dual-in-line	
Output Logic Form:	
Transistor-transistor logic	
nput Circuit Pattern:	
14 input	
Case Outline Source A	nd Designator:
D-3 mil-m-38510	
Terminal Surface Treat	ment:
Solder	
Voltage Rating And Typ	be Per Characteristic:
7.0 volts power source	
Time Rating Per Chacte	eristic:
100.00 nanoseconds pro	opagation delay time, low to high level output and 100.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type:	
Rom	
Memory Capacity:	
Unknown	
Test Data Document:	
96906-mil-std-883 standa	ard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Qua	antity:
24 printed circuit	
Shelf Life:	

N/a

NSN 5962-01-253-0169

Memory Microcircuit - Page 2 of 2

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0

